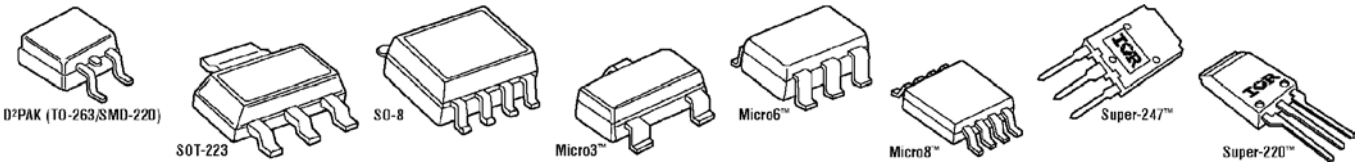


MOSFETs (Continued)



HEXFET™ Power MOSFETs — D*PAK (cont.) — NEW —
N-Channel (continued)

Mfr.'s Type	V(BR) _{oss} (V)	R _{DS(on)} (Ω)	I _D @ 25°C (A)	P _D (W)
IRF3710S	100	0.0250	57.00	3.80
IRF1310NS	100	0.0360	42.00	3.80
IRF540NS	100	0.0520	33.00	3.80
IRF530NS	100	0.1100	17.00	3.80
IRF3415S	150	0.0420	43.00	3.80
IRF3515S	150	0.0450	41.00	200.00
IRF3315S	150	0.0820	21.00	94.00
IRFS31N20D	200	0.0820	31.00	200.00
IRF640NS	200	0.1500	18.00	150.00
IRF630NS	200	0.3000	9.50	82.00
IRF644S	250	0.2800	14.00	125.00
IRF740S	400	0.5500	10.00	125.00
IRF710S	400	3.6000	2.00	36.00
IRF840S	500	0.8500	8.00	125.00
IRF830S	500	1.5000	4.50	74.00
IRF820S	500	3.0000	2.50	50.00
IRFBC40AS	600	1.2000	6.20	125.00
IRFBC40S	600	1.2000	6.20	130.00

P-Channel

IRF490SL	−55	0.0200	−74.00	200.00
IRF490SS	−55	0.0200	−74.00	3.80
IRF530SS	−55	0.0600	−31.00	110.00
IRF9224NS	−55	0.1750	−12.00	45.00
IRF9540NS	−100	0.1170	−23.00	3.80
IRF9530NS	−100	0.2000	−14.00	3.80
IRF9510S	−100	1.2000	−4.00	43.00
IRF6215S	−150	0.2900	−13.00	110.00
IRF9640S	−200	0.5000	−11.00	125.00
IRF9630S	−200	0.8000	−6.50	74.00

Logic Level N-Channel

IRL3502S	20	0.0070	110.00	140.00
IRL3102S	20	0.0130	61.00	89.00
IRL3803S	30	0.0060	140.00	200.00
IRL2203NS	30	0.0070	116.00	170.00
IRL3303S	30	0.0260	38.00	68.00
IRL1004S	40	0.0065	110.00	150.00
IRL2505S	55	0.0080	104.00	200.00
IRL3705NS	55	0.0100	89.00	170.00
IRL244NS	55	0.0220	47.00	110.00
IRL234NS	55	0.0350	30.00	68.00
IRL224NS	55	0.0600	18.00	45.00
IRL214S	60	0.2000	10.00	—
IRL2910S	100	0.0260	55.00	3.80
IRL540NS	100	0.0440	36.00	3.80
IRL530NS	100	0.1000	17.00	3.80
IRL520NS	100	0.1800	10.00	3.80
IRL640S	200	0.1800	17.00	125.00
IRL630S	200	0.4000	9.00	74.00

HEXFET™ Power MOSFETs — SOT-223

The SOT-223 package is capable of dissipating more than 1 W in a typical printed circuit board application. Package design allows for maximum die size, optimum thermal performance and ease of surface-mount manufacturing. Suitable for use with all soldering techniques.

N-Channel

Mfr.'s Type	V(BR) _{oss} (V)	R _{DS(on)} (Ω)	I _D @ 25°C (A)	P _D (W)
IRFL014N	55	0.1600	1.90	2.10
IRFL014	60	0.2000	5.20	2.00
IRFL4310	100	0.2000	2.20	2.10
IRFL110	100	0.5400	1.50	2.00
IRFL210	200	1.5000	0.96	2.00
IRFL214	250	2.0000	0.79	2.00

Logic Level N-Channel

IRLL3303	30	0.0310	6.50	2.10
IRLL2705	55	0.0400	5.20	2.10
IRLL014N	55	0.1400	2.00	1.00
IRLL014	60	0.2000	2.70	2.00
IRLL110	100	0.5400	1.50	2.00

HEXFET™ Power MOSFETs — SO-8

N-Channel

IRF7456	20	0.0065	16.00	2.50
IRF7455	30	0.0075	13.00	1.60

P-Channel

IRF7210	−12	0.0050	−16.00	2.50
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Logic Level N-Channel

IRF7401	20	0.0220	8.70	2.50
IRF7811A	28	0.0120	11.40	2.50
IRF7413	30	0.0110	12.00	2.50
Si4410DY	30	0.0135	10.0	2.50
IRF9410	30	0.0300	7.00	2.50
IRF7201	30	0.0300	7.00	2.50

Logic Level P-Channel

IRF7404	−20‡	0.0400	−5.30	2.50
IRF7416	−30	0.0200	−8.80	2.50
IRF7406	−30	0.0450	−4.70	2.50

Logic Level Dual N-Channel

IRF7311	20‡	0.0290	6.60	2.00
IRF7301	20‡	0.0500	4.30	2.00
IRF7101	20	0.1000	3.50	2.00
IRF7313	30	0.0290	7.00	2.00
IRF7303	30	0.0500	4.00	2.00
IRF7103	50	0.1300	3.00	2.00
IRF7341	55	0.0500	4.70	2.00

HEXFET™ Power MOSFETs — SO-8 (continued)

Logic Level Dual P-Channel

Mfr.'s Type	V(BR) _{oss} (V)	R _{DS(on)} (Ω)	I _D @ 25°C (A)	P _D (W)
IRF7324	−20‡	0.0260	9.00	2.00
IRF7314	−20	0.0580	−4.20	2.00
IRF7304	−20‡	0.0900	−3.60	2.00
IRF7316	−30	0.0580	−4.90	2.00
IRF7306	−30	0.1000	−3.60	2.00
IRF9953	−30	0.2500	−2.30	2.00
IRF7342	−55	0.1050	−3.40	2.00

Logic Level Dual N- and P-Channel

IRF7307	20‡	0.0500	4.30	1.40
	−20	0.0900	−3.60	1.40
IRF7105	25	0.1000	3.50	2.00
	−25	0.2500	−2.30	2.00
IRF7319	30	0.0290	6.50	2.00
	−30	0.0580	−4.90	2.00
IRF7309	30	0.0500	4.00	2.00
	−30	0.1000	−3.00	2.00
IRF9952	30	0.1000	3.50	2.00
	−30	0.2500	−1.80	2.00
IRF7343	55	0.0500	4.70	2.00
	−55	0.1050	−3.40	2.00

HEXFET™ Power MOSFETs — Micro3™

Logic Level N-Channel

IRLML2803TR	30	0.2500	0.91	540.00
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Logic Level P-Channel

IRLML5103TR	−30	0.6000	−0.60	540.00
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HEXFET™ Power MOSFETs — Micro6™

P-Channel

IRLMS6802TR	−20	0.0500	−5.60	2.00
Si3443DV	−20	0.0650	4.40	2.00
IRLMS5703TR	−30	0.2000	−1.60	1.70

HEXFET™ Power MOSFETs Micro8™

Logic Level Dual N- and P-Channel

IRF7507TR	20‡	0.1350	1.70	1.25
	−20	0.2700	−1.30	1.25
IRF7509TR	30	0.1350	1.70	1.25
	−30	0.2700	−1.20	1.25

HEXFET™ Power MOSFETs Super-247

N-Channel

IRFPS37N50A	500	0.1300	36.00	446.00
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HEXFET™ Power MOSFETs Super-220

N-Channel

IRFBA22N50A	500	0.2300	22.00	210.00
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*Also Available in D*PAK (TO-263/SMD-220). Add suffix S to the Mfr.'s Type Number. †Also available in D*PAK IRFS11N50A and IRFS9N60A. ‡Indicates "low VGS(th)" which can operate at VGS = 2.7 V.

Rectifiers



Silicon Standard Recovery Rectifiers — General Purpose Alloy Type

Mfr.'s Type*	V _{RRM} (V)	I _{FSM} (A)	I _{F(AV)} A @ Max. T _c (°C)	Package
1N3111	50	3000	150 @ 150	DO-30
150K5A†	50	3140	150 @ 150	DO-8
1N2054•	50	4500	250 @ 135	DO-9
300U5A†	50	5750	300 @ 130	DO-9
1N3288A†	100	2300	100 @ 130	DO-8
1N3085	100	3000	150 @ 150	DO-30
150K10A†	100	3140	150 @ 150	DO-8
150L10A†	100	3140	150 @ 150	DO-30
1N4045	100	5000	275 @ 120	DO-9
1N4046	150	5000	275 @ 120	DO-9
1N3289A†	200	2300	100 @ 130	DO-8

Mfr.'s Type*	V _{RRM} (V)	I _{FSM} (A)	I _{F(AV)} A @ Max. T _c (°C)	Package
150K20A†	200	3140	150 @ 150	DO-8
150L20A†	200	3140	150 @ 150	DO-30
1N4048	250	5000	275 @ 120	DO-9
1N3087	300	3000	150 @ 150	DO-30
150K30A†	300	3140	150 @ 150	DO-8
150L30A†	300	3140	150 @ 150	DO-30
1N4049	300	5000	275 @ 120	DO-9
300U30A†	300	5750	300 @ 130	DO-9
1N3088	400	3000	150 @ 150	DO-30
150K40A†	400	3140	150 @ 150	DO-8
150L40A†	400	3140	150 @ 150	DO-30

Mfr.'s Type*	V _{RRM} (V)	I _{FSM} (A)	I _{F(AV)} A @ Max. T _c (°C)	Package
1N4050	400	5000	275 @ 120	DO-9
1N4051	500	5000	275 @ 120	DO-9
1N3293A†	600	2300	100 @ 130	DO-8
1N4052	600	5000	275 @ 120	DO-9
300U60A†	600	5750	300 @ 130	DO-9
150K80A†	800	3140	150 @ 150	DO-8
300U80A†	800	5750	300 @ 130	DO-9
1N3295A†	1000	2300	100 @ 130	DO-8
1N4056	1000	5000	275 @ 120	DO-9
300U100A†	1000	5750	300 @ 130	DO-9
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*Cathode-to-stud; for anode-to-stud, add "R" to basic number (example: 1N3289AR, 1N3111R, 150LR5A). †Also available in stud-topped case and flag terminal. ‡1N3288 series also available. •1N3735 series also available. *